



## Revision History

<u>Rev. No.</u>	<u>History</u>	<u>Issue Date</u>	<u>Remark</u>
2.0	Initial issue with new naming rule	Mar. 01, 2005	
2.1	Revise 1. page 2 & 4: page address inputs 2. Add Vcc absolute max. in page 5	Nov. 23, 2005	
2.2	Modify Deep Power Down Mode & Page Mode	Jun. 15, 2006	
2.3	Revise DC/AC Char.	Oct. 29, 2007	
2.4	Change wafer process from 0.13um to 90nm	Aug. 26, 2008	
2.5	Add 48BGA-6*8mm package	Jan. 06, 2010	
2.6	Delete Die form information	Apr.12,2010	
2.7	Add the 48BGA-6*8mm package dimensions: D2 and E2	Aug.26,2010	

### ■ Product Description

The CS26LV32163 is a 32M-bit PSRAM organized as 2M words by 16 bits. It provides high density, high speed and low power. The device operates single power supply. The device also features SRAM-like W/R timing whereby the device is controlled by /CE, /OE and /WE on asynchronous. The device has the page access operation. Page size is 16 words. The device also supports deep power-down mode, realizing low-power standby. The CS26LV32163 is available die form and 48-Ball BGA package.

### ■ Features

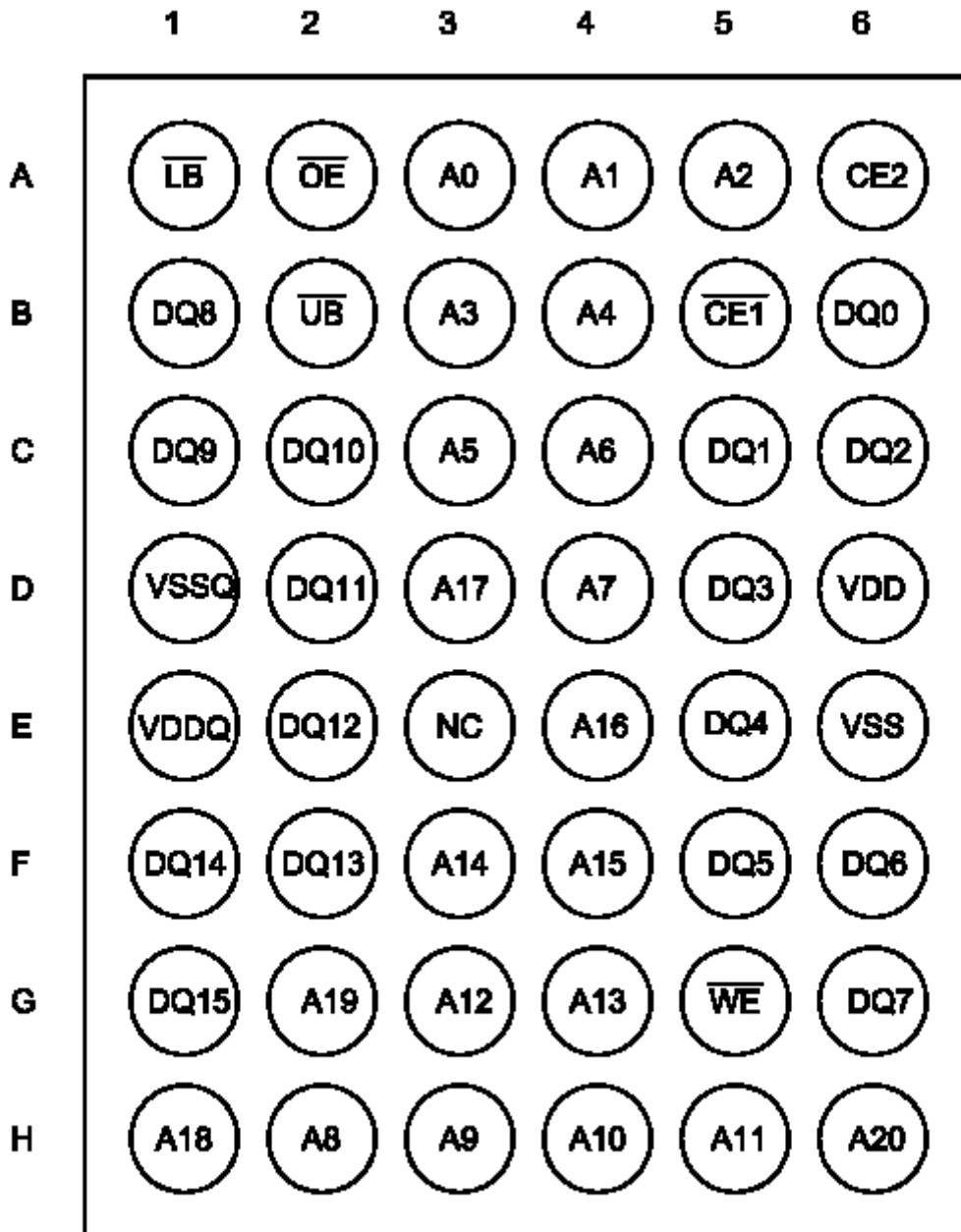
- Single power supply voltage of 2.6 to 3.3V
- Direct TTL compatibility for all inputs and outputs.
- Deep power-down mode : Memory cell data invalid.
- Page operation mode
  - Page read operation by 16 words.
- Logic compatible with SRAM R/W pin.
- Standby Current
  - Standby 120 uA(Max)
  - Deep power-down standby 10 uA(Max)
- Access Time
  - /CE1 Access Time: 70ns
  - /OE Access Time: 25ns
  - Page Access Time: 20ns

### ■ Product Family

Product Family	Operating Temp	Vcc. Range	Speed(ns)	Standby(Max.)	Package Type
CS26LV32163	0~70°C	2.6~3.3	70	120 uA	Dice
	-40~85°C				48BGA-6*7mm
					48BGA-6*8mm

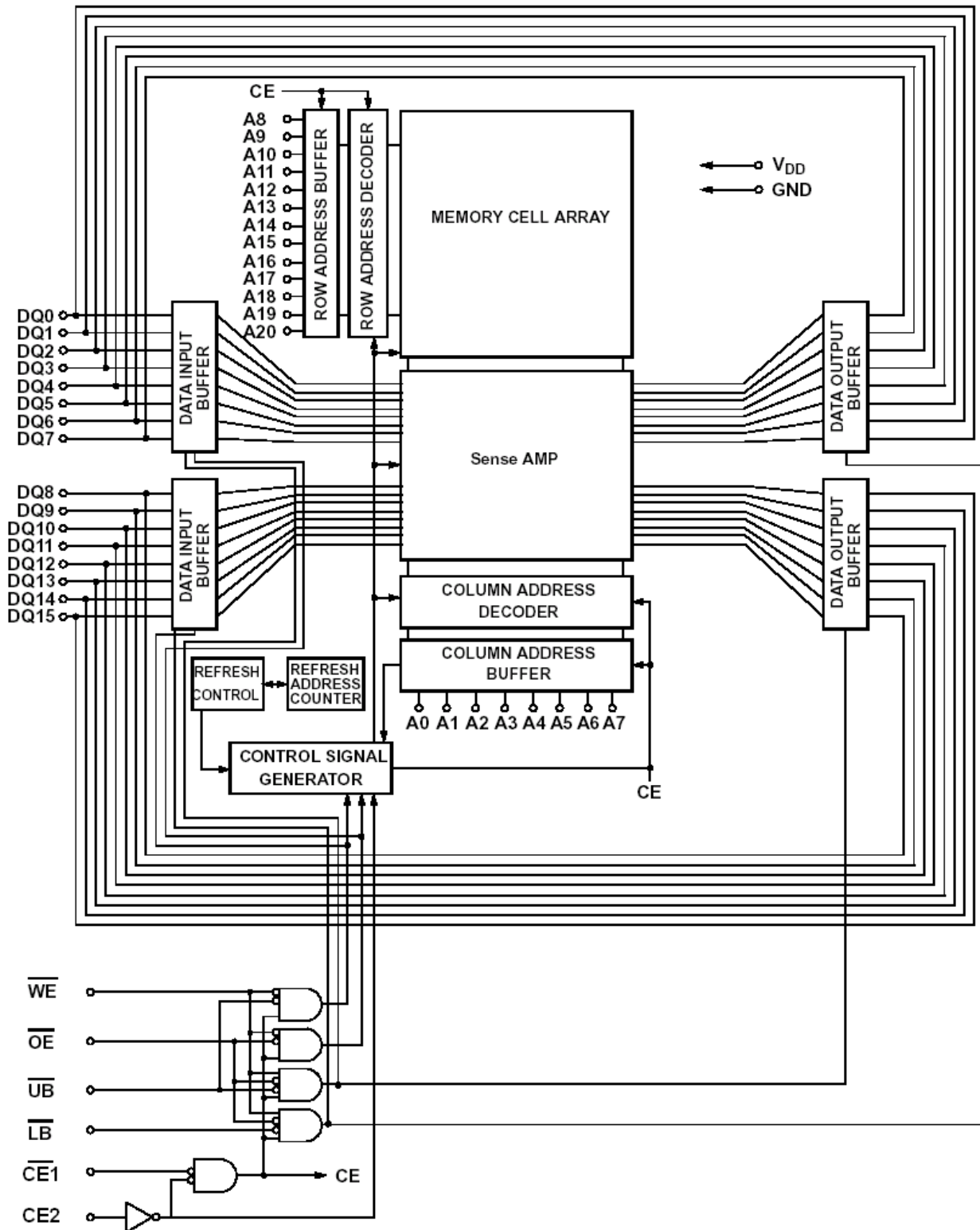
■ Pin Configuration

<48BGA>



**48 BGA - Top View**

### ■ Functional Block Diagram





# Low Power Pseudo SRAM

2 M Word x 16 bit

CS26LV32163

## Pin Descriptions

Name	Type	Function
A0~A20	input	Address input
A0~A3	input	Page Address input
/CE1	input	Chip Enable Input1, Low : Enable
CE2	input	Chip Enable Input2, High:Enable, Low:Enter Power Down mode
/WE	input	Write Enable input, Low :Enable
/OE	input	Output Enable input, Low :Enable
/LB	input	Lower byte write control
/UB	input	Upper byte write control
DQ0~DQ15	I/O	Data inputs/outputs
V <sub>DD</sub>	Power	Device Power supply
V <sub>SS</sub>	Power	VSS must be connected ground
V <sub>DDQ</sub>	Power	I/O Power supply
V <sub>SSQ</sub>	Power	VSSQ must be connected ground
NC		Not Connection

## Truth Table

MODE	/CE1	CE2	/OE	/WE	/LB	/UB	DQ0~7	DQ8~15	V <sub>DD</sub> Current
Deep power down	X	L	X	X	X	X	High Z	High Z	
Standby	H	H	X	X	X	X	High Z	High Z	I <sub>CCSB</sub> , I <sub>CCSB1</sub>
Output Disabled	L	H	H	H	X	X	High Z	High Z	I <sub>CC</sub>
Read	L	H	L	H	L	L	D <sub>OUT</sub>	D <sub>OUT</sub>	I <sub>CC</sub>
Upper Byte Read					L	H	D <sub>OUT</sub>	High Z	I <sub>CC</sub>
Lower Byte Read					H	L	High Z	D <sub>OUT</sub>	I <sub>CC</sub>
Write	L	H	X	L	L	L	D <sub>IN</sub>	D <sub>IN</sub>	I <sub>CC</sub>
Upper Byte Write					L	H	D <sub>IN</sub>	Invalid	I <sub>CC</sub>
Lower Byte Write					H	L	Invalid	D <sub>IN</sub>	I <sub>CC</sub>

Note: X means don't care. (Must be low or high state)

### ■ Absolute Maximum Ratings<sup>(1)</sup>

Symbol	Parameter	Rating	Unit
V <sub>IN</sub>	Input Voltage	-1.0 to 3.6	V
V <sub>OUT</sub>	Output Voltage	-1.0 to 3.6	V
V <sub>DD</sub>	Device Power Supply Voltage	-1.0 to 3.6	V
T <sub>STG</sub>	Storage Temperature	-55 to +150	°C
T <sub>A</sub>	Operating Temperature	-40 to +85	°C
P <sub>D</sub>	Power Dissipation	0.6	W

1. Stresses greater than those listed above “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

### ■ DC Electrical Characteristics ( T<sub>A</sub> = 0 to + 70°C , V<sub>DD</sub>= 3.0V )

Parameter Name	Parameter	Test Conduction	MIN	TYP <sup>(1)</sup>	MAX	Unit
V <sub>IL</sub>	Input Low Voltage <sup>(2)</sup>		-0.3		0.6	V
V <sub>IH</sub>	Input High Voltage <sup>(2)</sup>		2.4		V <sub>DD</sub> + 0.3	V
I <sub>IL</sub>	Input Leakage Current	V <sub>IN</sub> =0 to V <sub>DD</sub>	-1		1	uA
I <sub>OL</sub>	Output Leakage Current	Output disable, V <sub>OUT</sub> = 0V to V <sub>DD</sub>	-1		1	uA
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 0.5mA, V <sub>DD</sub> =V <sub>DD</sub> min			0.6	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -0.5mA	2.4			V
I <sub>CC1</sub>	Operating Current	t <sub>RC</sub> = Min, /CE1=V <sub>IL</sub> , CE2=V <sub>IH</sub> , I <sub>OUT</sub> =0mA			25	mA
I <sub>CC2</sub>	Page Access Operating current	t <sub>PC</sub> = Min, /CE1=V <sub>IL</sub> , CE2=V <sub>IH</sub> , I <sub>OUT</sub> =0mA, Page add. cycling.			15	mA
I <sub>CCSB1</sub>	Standby Current -CMOS	/CE1 ≥ V <sub>DD</sub> -0.2V, CE2=V <sub>DD</sub> -0.2V			120	uA
I <sub>CCSB2</sub>	Deep Power-down Standby Current	CE2 = 0.2V			10	uA

1. Typical characteristics are at T<sub>A</sub> = 25°C.
2. V<sub>IH</sub>(Max) V<sub>DD</sub>+1.0V with 10ns pulse width, V<sub>IL</sub>(Min)-1.0V with 10ns pulse width

### ■ Capacitance <sup>(1)</sup> (TA = 25°C, f = 1.0 MHz)

Symbol	Parameter	Conditions	MAX.	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> =0V	10	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>OUT</sub> =0V	10	pF

1. This parameter is sampled periodically and is not 100% tested

### ■ AC Test Conditions

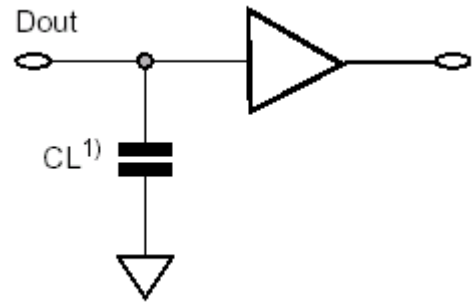
Test Conditions (Test Load and Test Input/Output Reference)

Input Pulse Level : 0.2V to V<sub>DDQ</sub>-0.2V

Input Rise and Fall Time : 5ns

Input and Output reference Voltage : V<sub>DDQ</sub> /2

Output Load (See right) : CL1) = 30pF



1. Including scope and Jig capacitance

### ■ Key To Switching Waveforms

Waveform	Inputs	Outputs
	Must be standby	Must be standby
	May change for H to L	Will be change from H to L
	May change for L to H	May change for L to H
	Don't care any change permitted	Change state unknown
	Does not apply	Center line is high impedance "OFF" state



# Low Power Pseudo SRAM

2 M Word x 16 bit

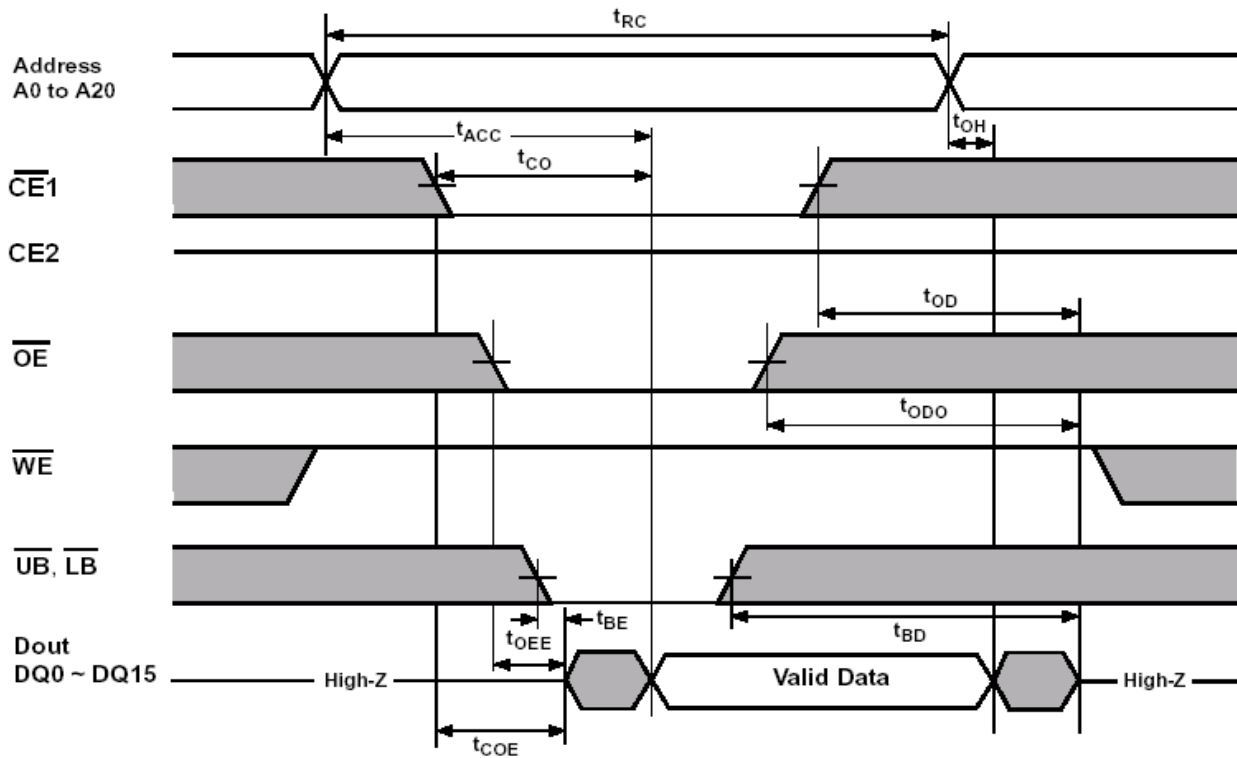
CS26LV32163

## ■ AC Characteristics <Read cycle & Write Cycle>

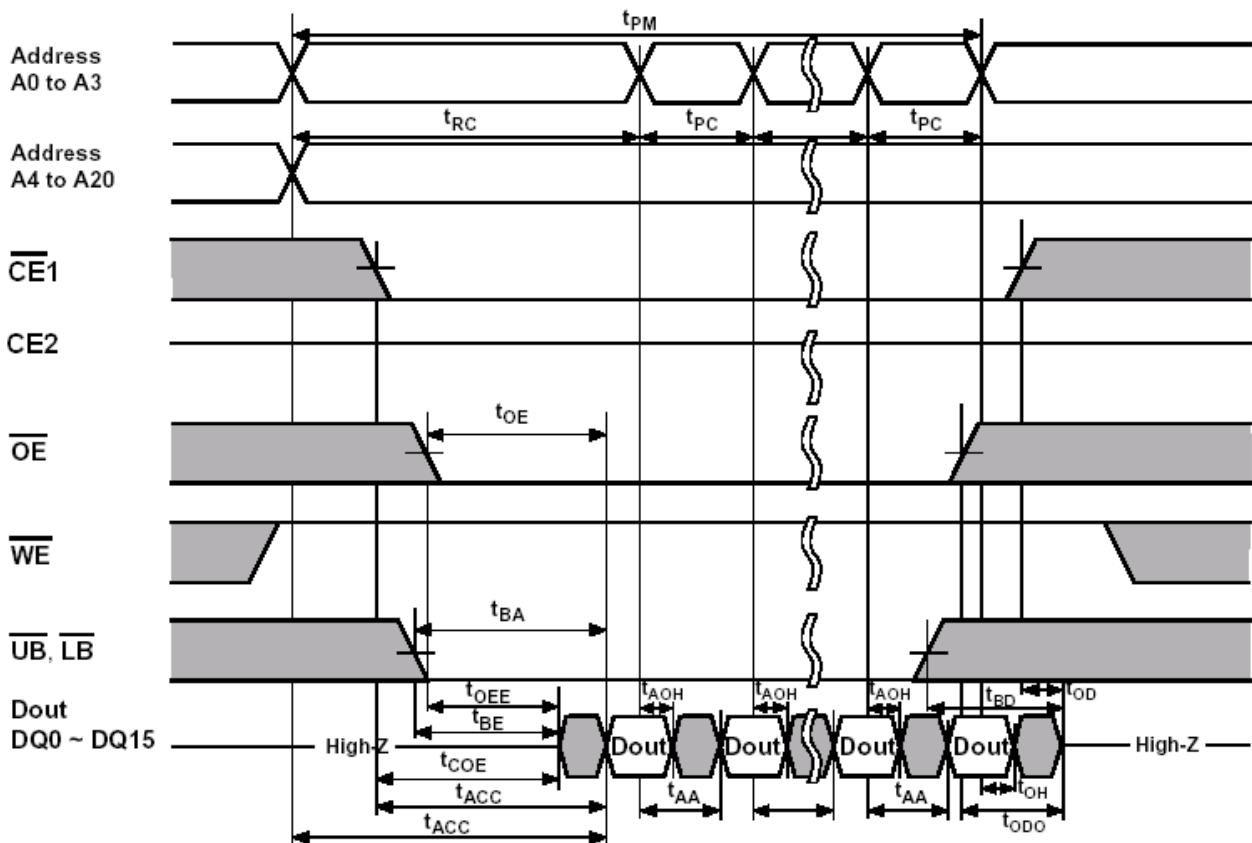
Parameter Name	Name	70		Unit
		Min	Max	
Read cycle time	$t_{RC}$	70	10,000	ns
Page mode cycle time	$t_{MRC}$	20	10,000	ns
Address access time	$t_{ACC}$	-	70	ns
Page Address Access Time	$t_{AA}$		20	ns
Chip enable access time (/CE1)	$t_{CO}$	-	70	ns
Output enable to output valid (/OE)	$t_{OE}$	-	25	ns
Byte enable access time	$t_{BA}$	-	25	ns
Output data hold time	$t_{OH}$	5	-	ns
Page mode output data hold time	$t_{AOH}$	5	-	ns
Chip enable to output in low Z (/CE1)	$t_{COE}$	10	-	ns
Output enable to output in low Z (/OE)	$t_{OEE}$	0	-	ns
Byte enable to output in low Z	$t_{BE}$	0	-	ns
Chip disable to output in High Z (/CE1)	$t_{OD}$	-	20	ns
Output disable to output in High Z (OE)	$t_{ODO}$	-	20	ns
Byte disable to output in High Z	$t_{BD}$	-	20	ns
Write cycle time	$t_{WC}$	70	10,000	ns
Byte enable to end of write	$t_{BW}$	60	-	ns
Address valid to end of write	$t_{AW}$	60	-	ns
Chip select to end of write	$t_{CW}$	65	-	ns
Data set up time	$t_{DS}$	30	-	ns
Data hold time	$t_{DH}$	0	-	ns
Write pulse width	$t_{WP}$	50	-	ns
Address set up time	$t_{AS}$	0	-	ns
Write recovery time(/WE)	$t_{WR}$	0	-	ns
/WE high to output low Z	$t_{OEW}$	0	-	ns
/WE low to output high Z	$t_{ODW}$	-	20	ns
Chip enable high pulse width	$t_{CEH}$	10		ns
Write enable high pulse width	$t_{WEH}$	6	-	ns
CE2 set –up time	$t_{CS}$	0	-	ns
CE2 hold time	$t_{CH}$	300	-	ns
CE2 pulse width	$t_{DPD}$	10	-	ns
CE2 hold from /CE1	$t_{CHC}$	0	-	ns
CE2 hold from power on	$t_{CHP}$	30	-	ns



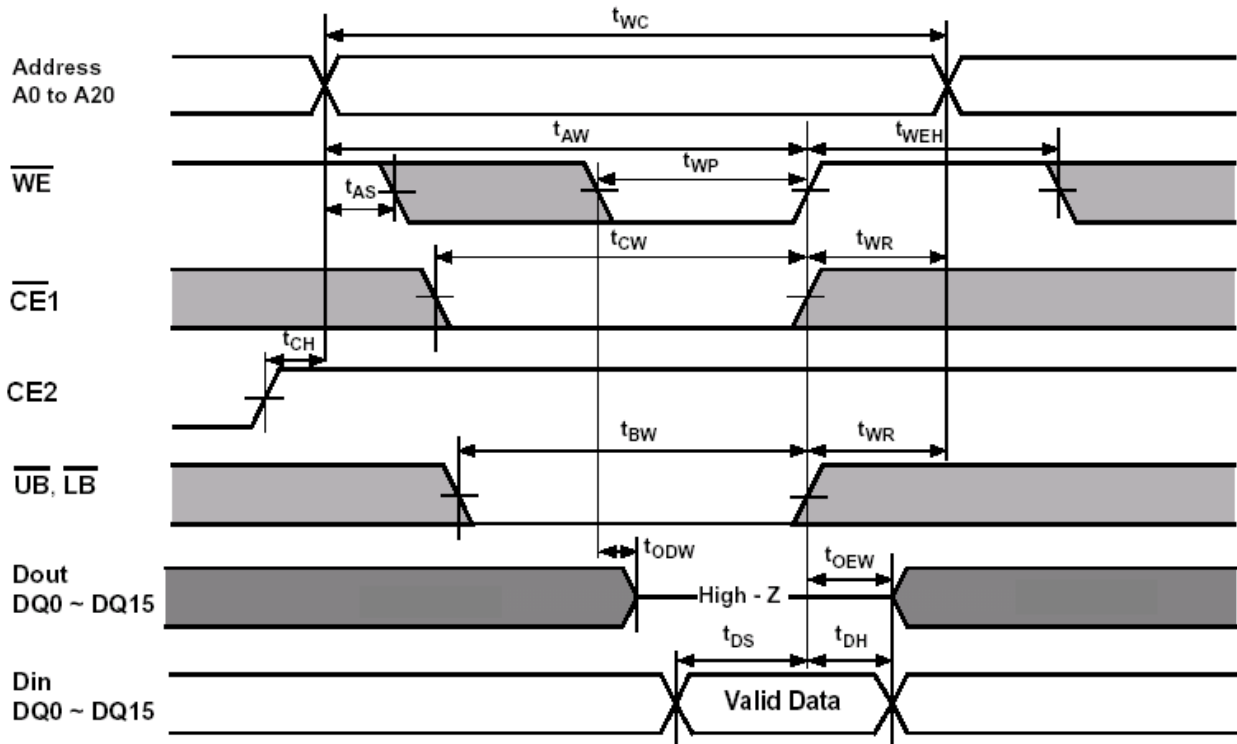
## TIMING DIAGRAMS <READ CYCLE>



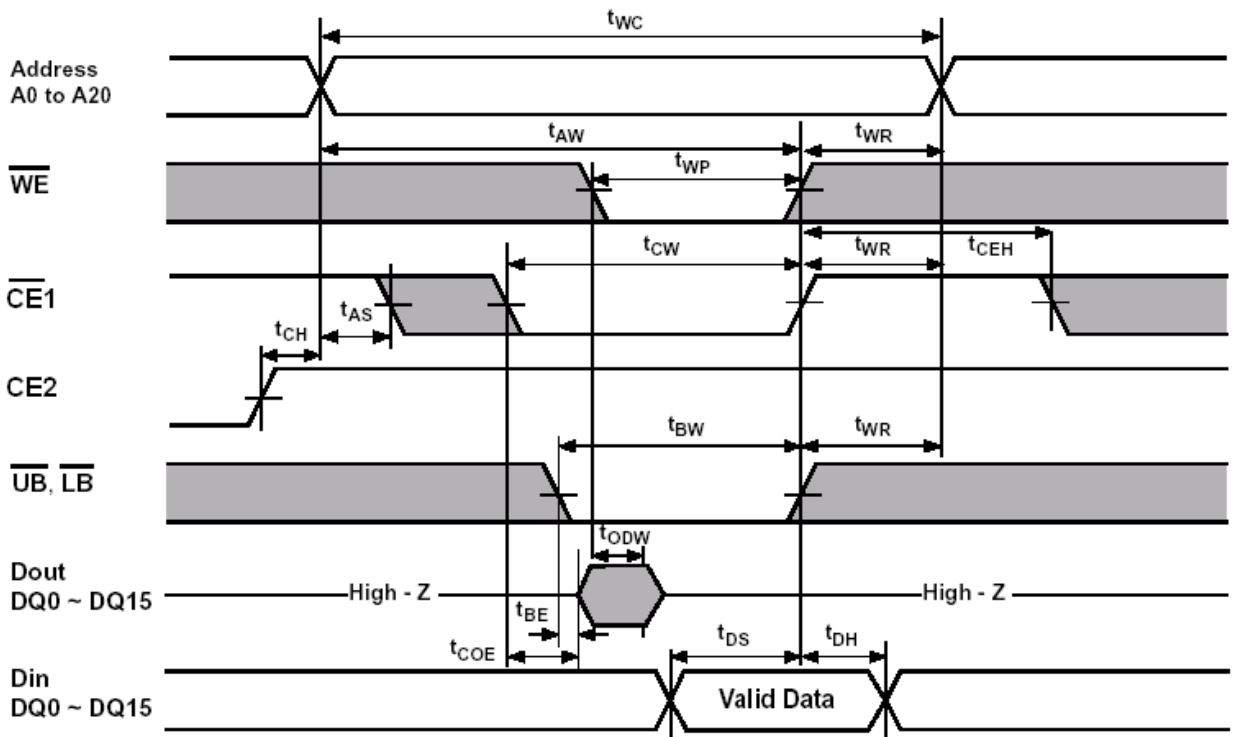
## PAGE READ CYCLE (16 words access)



## WRITE CYCLE (1) (/WE controlled)



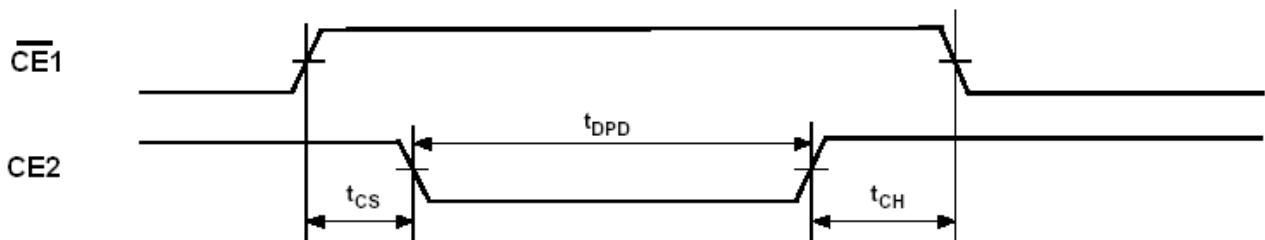
## WRITE CYCLE (2) (/CE1 controlled)



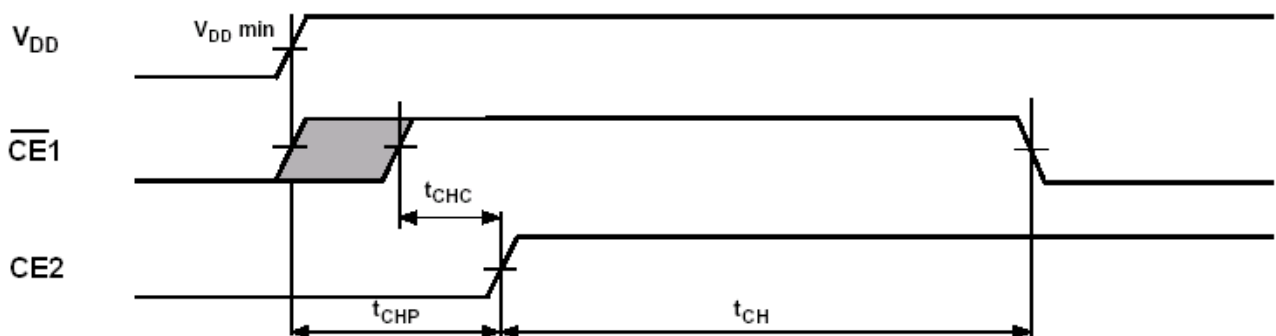
NOTES

1. AC measurement are assumed  $t_R, t_F = 5ns$ .
1. Parameters  $t_{OD}, t_{ODO}, t_{BD}$  and  $t_{ODW}$  define the time at which the output goes the open condition and are not output voltage reference levels.
2. Data cannot be retained at deep power-down stand-by mode.
3. If  $/OE$  is high during the write cycle, the outputs will remain at high impedance.
4. During the output state of DQ signals, input signals of reverse polarity must not be applied.
5. If  $/CE1$  or  $/LB\&/UB$  goes LOW coincident with or after  $/WE$  goes LOW, the outputs will remain at high impedance.
6. If  $/CE1$  or  $/LB\&/UB$  goes HIGH coincident with or before  $/WE$  goes HIGH, the outputs will remain at high impedance.

■ DEEP POWER-DOWN TIMING



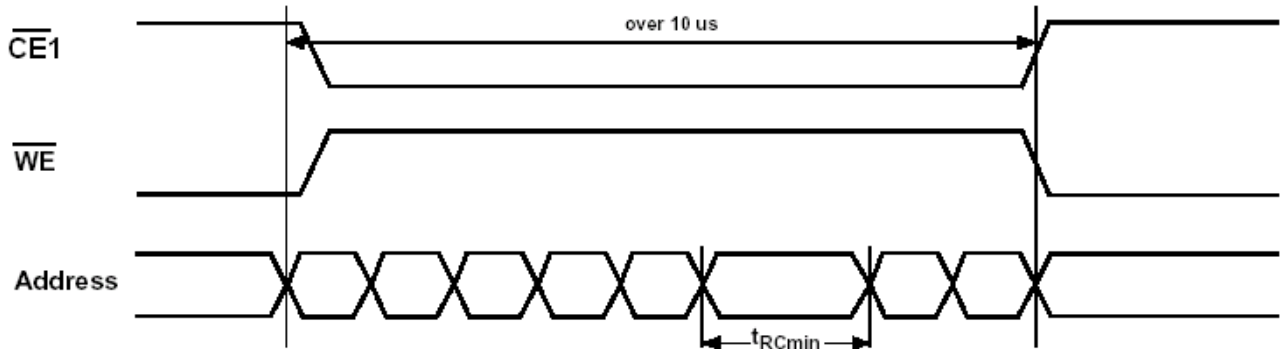
■ POWER\_ON TIMING



## ■ PROVISIONS OF ADDRESS SKEW

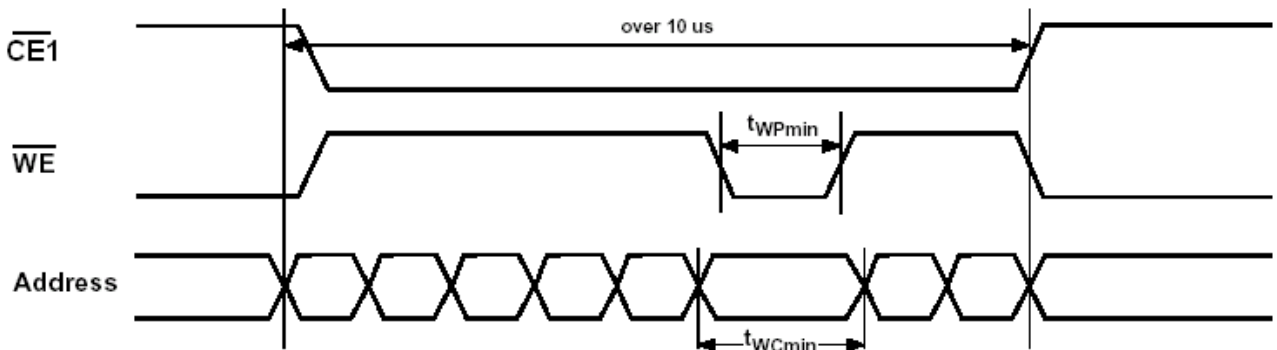
### Read

In case, multiple invalid address cycles shorter than  $t_{RC\_min}$  sustain over 10us in a active status, as least one valid address cycle over  $t_{RC\_min}$  must be needed during 10us.



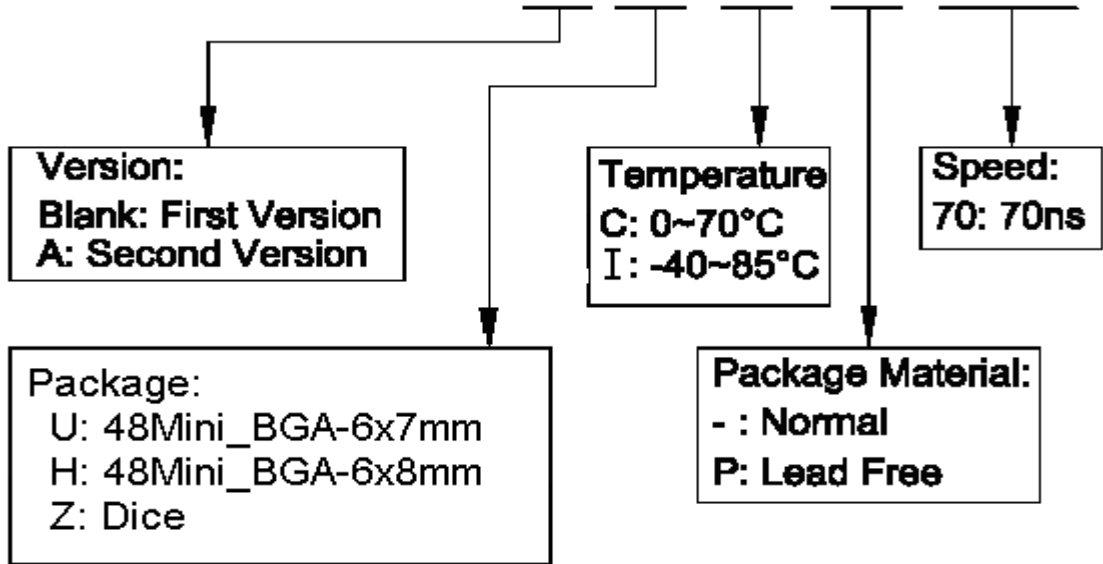
### Write

In case, multiple invalid address cycles shorter than  $t_{WC\_min}$  sustain over 10us in a active status, as least one valid address cycle over  $t_{RC\_min}$  with  $t_{WP\_min}$  must be needed during 10us.



■ Order information

**CS26LV32163X X X X XX**



Note: Package material code "P" meets RoHS